General Purpose Transistors

PNP Silicon

Features

• These are Pb-Free Devices*



Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-60	Vdc
Collector – Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	۱ _C	-600	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above 25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

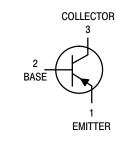
DEVICE MARKING

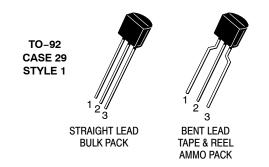
Device	Line 1	Line 2
MPS2907AG	MPS	2907A
MPS2907ARLG	MPS2	907A
MPS2907ARLRAG	MPS	2907
MPS2907ARLRPG	MPS	2907



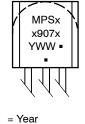
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MARKING DIAGRAM



WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

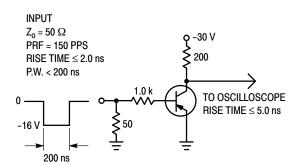
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

Ch	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage	(Note 1) (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-60	-	Vdc
Collector - Base Breakdown Voltage (Ic	_c = -10 μAdc, I _E = 0)	V _{(BR)CBO}	-60	-	Vdc
Emitter-Base Breakdown Voltage (I _E =	= –10 μAdc, I _C = 0)	V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CE} = -30 Vd	c, V _{EB(off)} = -0.5 Vdc)	I _{CEX}	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$		I _{CBO}	-	-0.01 -10	μAdc
Base Current (V _{CE} = -30 Vdc, V _{EB(off)}	= -0.5 Vdc)	IB	-	-50	nAdc
ON CHARACTERISTICS					÷
$ \begin{array}{l} DC \ Current \ Gain \\ (I_C = -0.1 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -1.0 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -10 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -150 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -500 \ mAdc, \ V_{CE} = -10 \ Vdc) \end{array} $		h _{FE}	75 100 100 100 50	- - 300 -	_
Collector – Emitter Saturation Voltage (Note 1) ($I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc}$)		V _{CE(sat)}		-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 1) ($I_C = -150$ mAdc, $I_B = -15$ mAdc) ($I_C = -500$ mAdc, $I_B = -50$ mAdc)		V _{BE(sat)}		-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTIC	8	1			
Current-Gain – Bandwidth Product (N $(I_C = -50 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f = -20 $		f _T	200	-	MHz
Output Capacitance ($V_{CB} = -10$ Vdc, I_{E}	= 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C	= 0, f = 1.0 MHz)	C _{ibo}	-	30	pF
SWITCHING CHARACTERISTICS					
Turn–On Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc},$	t _{on}	-	45	ns
Delay Time	I _{B1} = -15 mAdc) (Figures 1 and 5)	t _d	-	10	ns
Rise Time		t _r	-	40	ns
Turn-Off Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc},$	t _{off}	-	100	ns
Storage Time	I _{B1} = I _{B2} = 15 mAdc) (Figure 2)		-	80	ns
Fall Time		t _f	-	30	ns

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



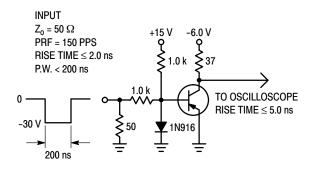
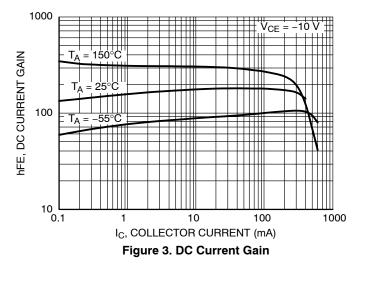
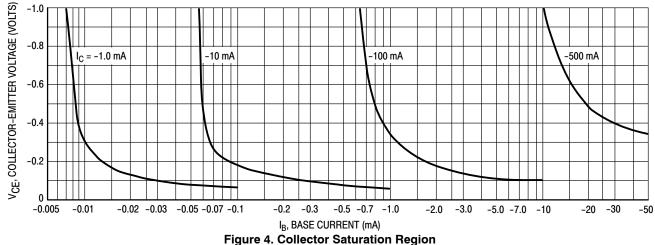




Figure 2. Storage and Fall Time Test Circuit



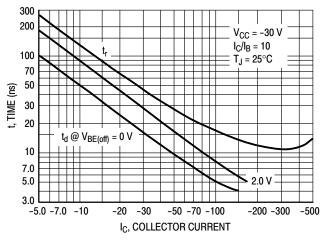
TYPICAL CHARACTERISTICS



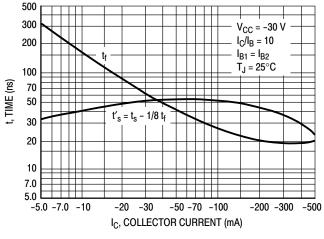
ORDERING INFORMATION

Device	Package	Shipping [†]	
MPS2907AG	TO-92 (Pb-Free)	5000 Units / Bulk	
MPS2907ARLG	TO-92 (Pb-Free)	– 2000 / Tape & Reel	
MPS2907ARLRAG	TO-92 (Pb-Free)		
MPS2907ARLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack	

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



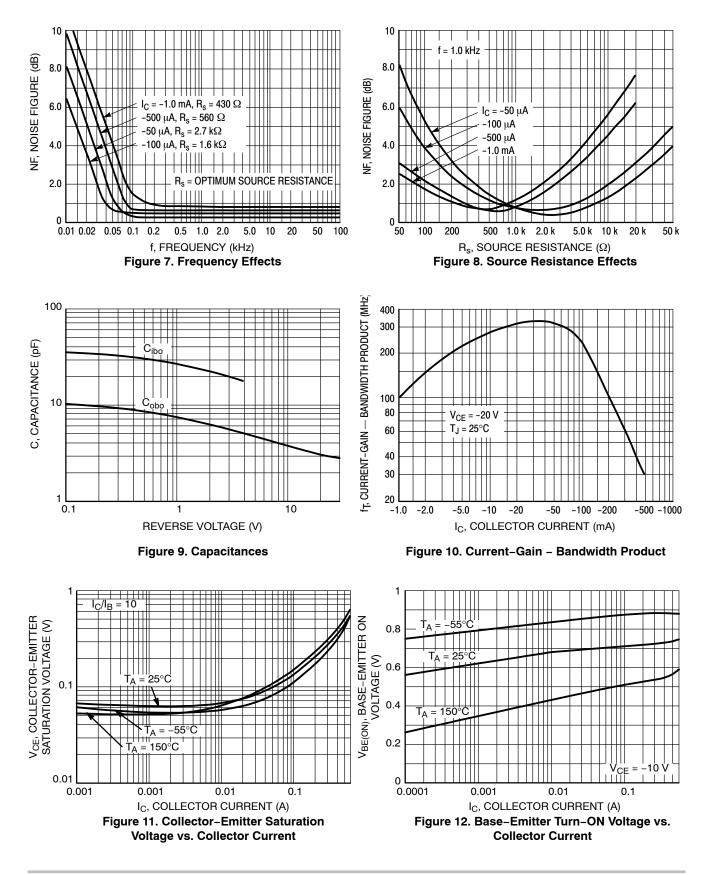


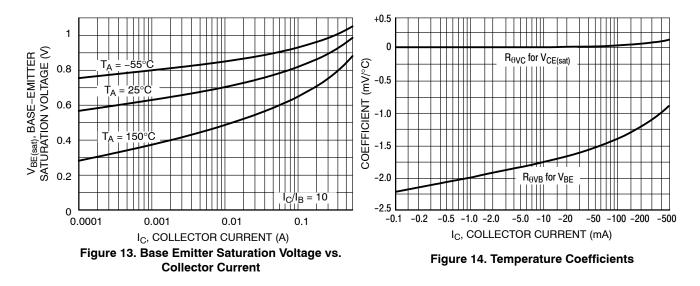




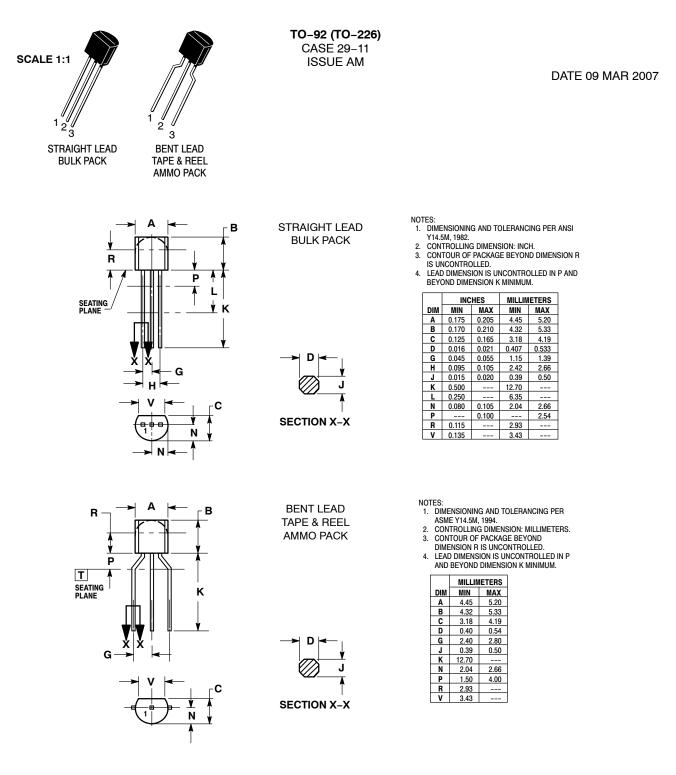
TYPICAL SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 V_{CE} = 10 Vdc, T_A = 25°C





ONSEMI,



STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11 **ISSUE AM**

STYLE 3: PIN 1. ANODE

DATE 09 MAR 2007

	EMITTER BASE COLLECTOR
STYLE 6: PIN 1. 2. 3.	SOURCE & SUBSTRATE
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
STYLE 26: PIN 1. 2. 3.	V _{CC} GROUND 2

	BASE EMITTER COLLECTOR
2.	SOURCE DRAIN GATE
2.	MAIN TERMINAL 1 Gate Main Terminal 2
2.	COLLECTOR BASE EMITTER
2.	SOURCE GATE DRAIN
STYLE 32: PIN 1.	BASE

2. COLLECTOR 3. EMITTER

	ANODE ANODE CATHODE
2.	DRAIN GATE SOURCE & SUBSTRATE
2.	3: ANODE 1 GATE CATHODE 2
2.	B: ANODE CATHODE NOT CONNECTED
2.	3: GATE SOURCE DRAIN
STYLE 2	B:

PIN 1. CATHODE ANODE
GATE

STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT

2.	CATHODE CATHODE ANODE
2.	BASE 1 EMITTER BASE 2
2.	EMITTER COLLECTOR BASE
2.	EMITTER COLLECTOR/ANODE CATHODE
2.	NOT CONNECTED ANODE CATHODE
2.	INPUT GROUND LOGIC

STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED CATHODE ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR

3. EMITTER

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